

MICROWAVE LOW NOISE AMPLIFIER
NPN SILICON EPITAXIAL TRANSISTOR

DESCRIPTION

The 2SC3356 is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

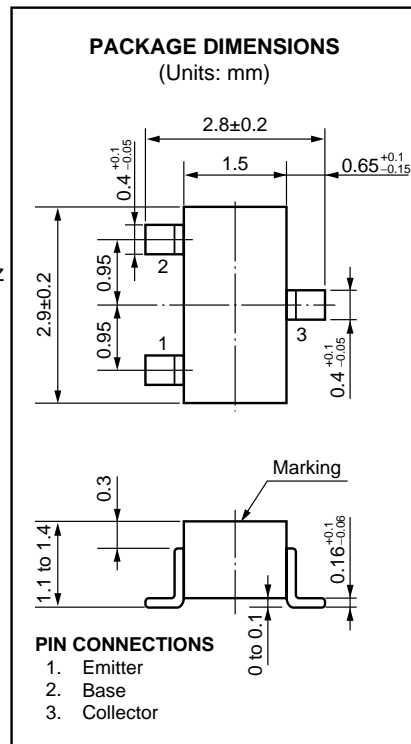
It has dynamic range and good current characteristic.

FEATURES

- Low Noise and High Gain
NF = 1.1 dB TYP., $G_a = 11$ dB TYP. @ $V_{CE} = 10$ V, $I_c = 7$ mA, $f = 1.0$ GHz
- High Power Gain
MAG = 13 dB TYP. @ $V_{CE} = 10$ V, $I_c = 20$ mA, $f = 1.0$ GHz

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_c	100	mA
Total Power Dissipation	P_T	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65 to +150	°C



ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			1.0	μA	$V_{CB} = 10$ V, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			1.0	μA	$V_{EB} = 1.0$ V, $I_C = 0$
DC Current Gain	h_{FE}^*	50	120	300		$V_{CE} = 10$ V, $I_c = 20$ mA
Gain Bandwidth Product	f_T		7		GHz	$V_{CE} = 10$ V, $I_c = 20$ mA
Feed-Back Capacitance	C_{re}^{**}		0.55	1.0	pF	$V_{CB} = 10$ V, $I_E = 0$, $f = 1.0$ MHz
Insertion Power Gain	$ S_{21e} ^2$		11.5		dB	$V_{CE} = 10$ V, $I_c = 20$ mA, $f = 1.0$ GHz
Noise Figure	NF		1.1	2.0	dB	$V_{CE} = 10$ V, $I_c = 7$ mA, $f = 1.0$ GHz

* Pulse Measurement $PW \leq 350$ μs , Duty Cycle ≤ 2 %

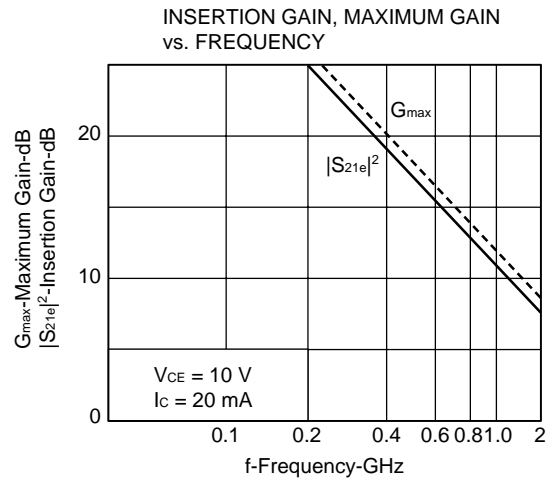
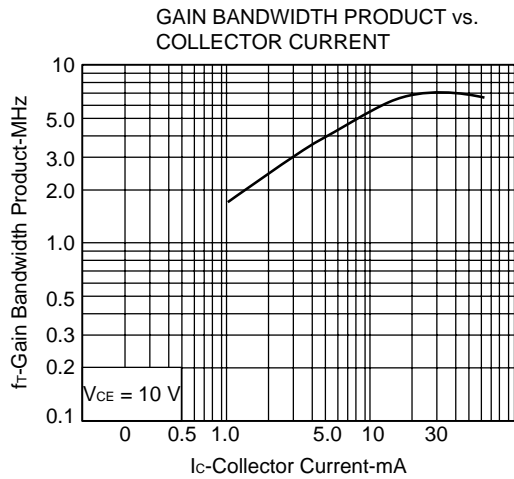
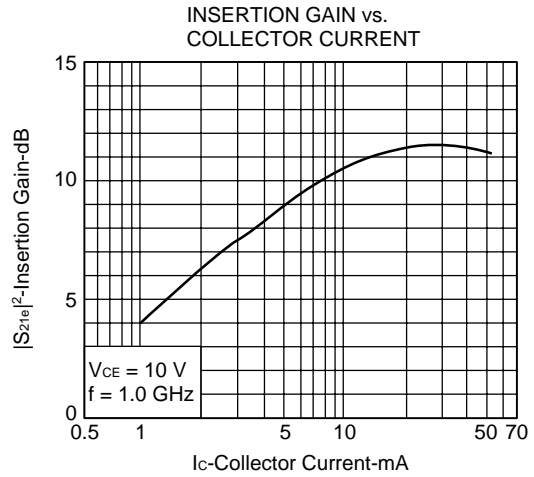
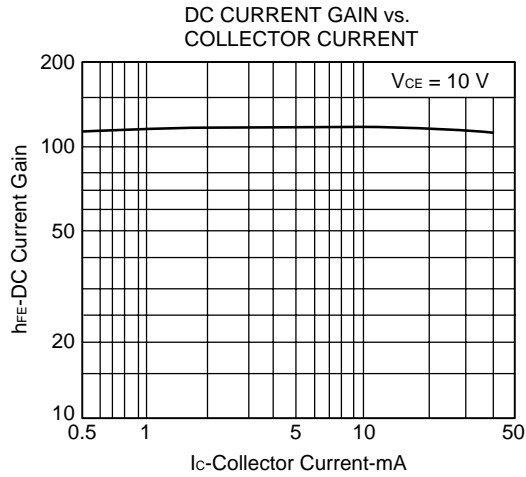
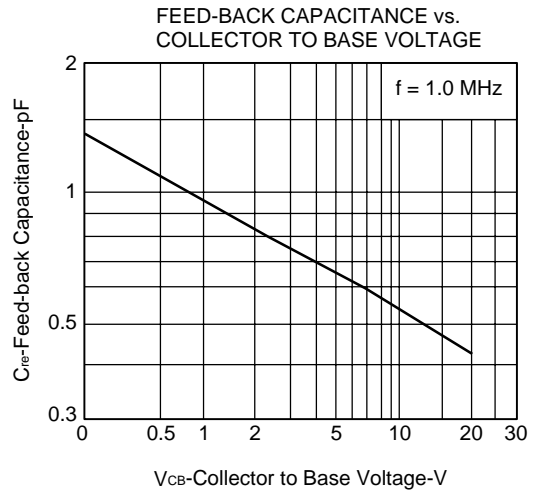
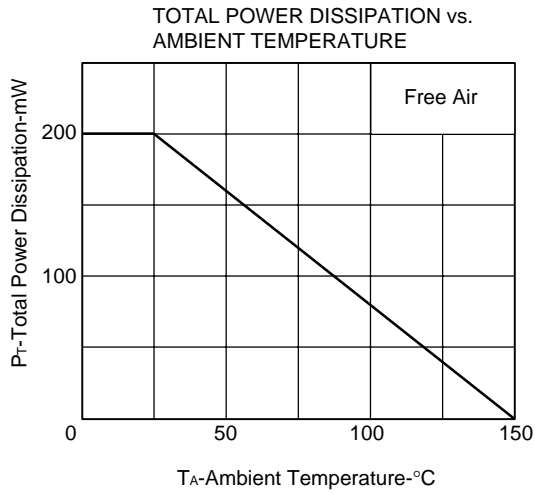
** The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

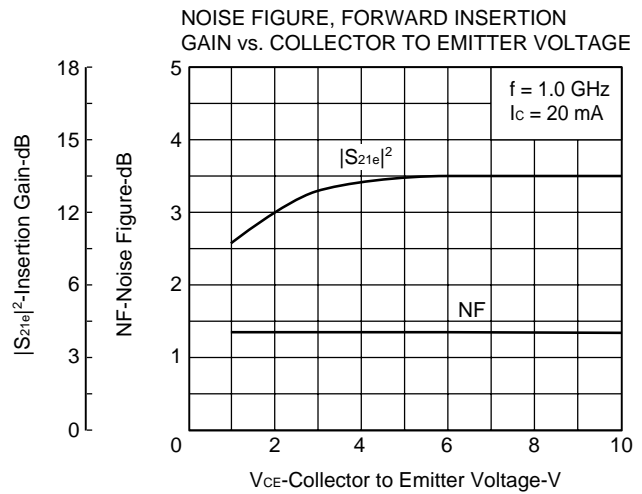
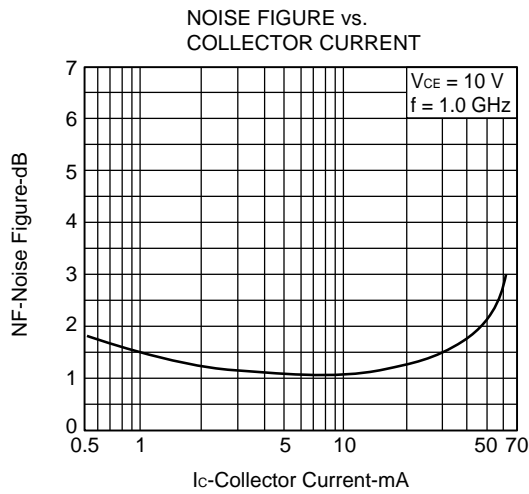
h_{FE} Classification

Class	R23/Q *	R24/R *	R25/S *
Marking	R23	R24	R25
h_{FE}	50 to 100	80 to 160	125 to 250

* Old Specification / New Specification

TYPICAL CHARACTERISTICS (T_A = 25 °C)





S-PARAMETER

$V_{CE} = 10\text{ V}$, $I_c = 5\text{ mA}$, $Z_o = 50\ \Omega$

f (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
200	0.651	-69.3	10.616	129.3	0.051	59.2	0.735	-28.1
400	0.467	-113.3	6.856	104.4	0.071	54.4	0.550	-34.1
600	0.391	-139.3	4.852	90.9	0.086	56.0	0.468	-33.9
800	0.360	-159.2	3.802	81.2	0.101	59.1	0.426	-33.6
1000	0.360	-176.9	3.098	72.9	0.118	61.0	0.397	-35.7
1200	0.361	172.7	2.646	67.3	0.137	63.5	0.373	-38.3
1400	0.381	160.3	2.298	59.3	0.157	63.3	0.360	-43.0
1600	0.398	152.2	2.071	55.2	0.180	64.1	0.337	-45.9
1800	0.423	143.3	1.836	49.0	0.203	63.7	0.320	-52.3
2000	0.445	137.6	1.689	46.2	0.220	64.7	0.302	-52.2

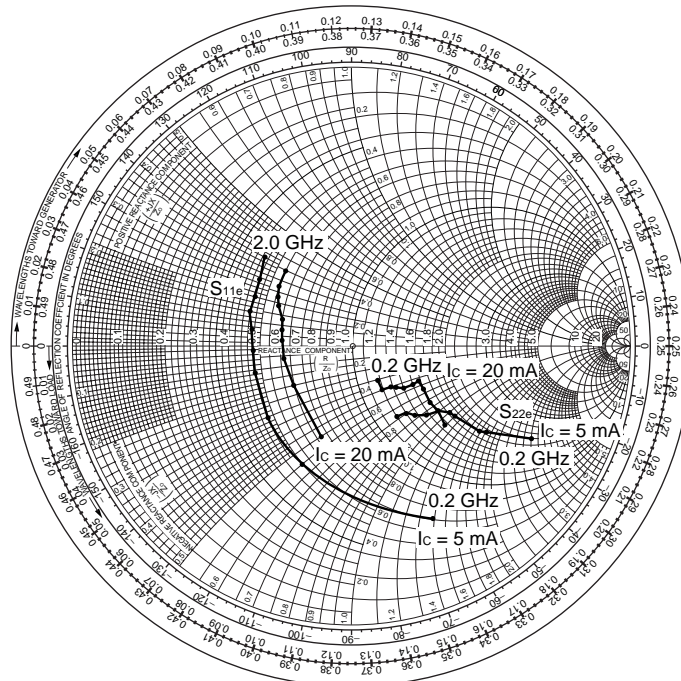
$V_{CE} = 10\text{ V}$, $I_c = 5\text{ mA}$, $Z_o = 50\ \Omega$

f (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
200	0.339	-107.0	16.516	108.7	0.035	66.1	0.459	-36.6
400	0.258	-147.3	8.928	92.1	0.060	71.0	0.343	-32.9
600	0.243	-167.7	6.022	83.0	0.085	71.9	0.305	-29.9
800	0.242	177.0	4.633	76.2	0.109	72.2	0.284	-29.4
1000	0.260	164.5	3.744	69.9	0.136	70.4	0.266	-31.7
1200	0.269	157.6	3.193	65.7	0.160	69.9	0.246	-35.0
1400	0.294	148.7	2.750	58.8	0.187	66.7	0.233	-40.4
1600	0.314	143.1	2.479	55.5	0.212	65.2	0.208	-43.6
1800	0.343	136.5	2.185	50.1	0.238	62.4	0.190	-50.5
2000	0.367	131.4	2.016	47.8	0.254	61.6	0.173	-48.3

S-PARAMETER

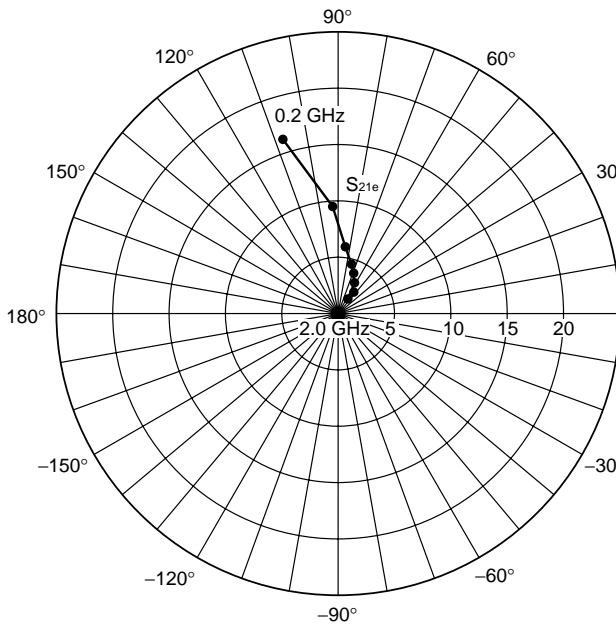
S_{11e}, S_{22e}-FREQUENCY

CONDITION V_{CE} = 10 V
200 MHz Step



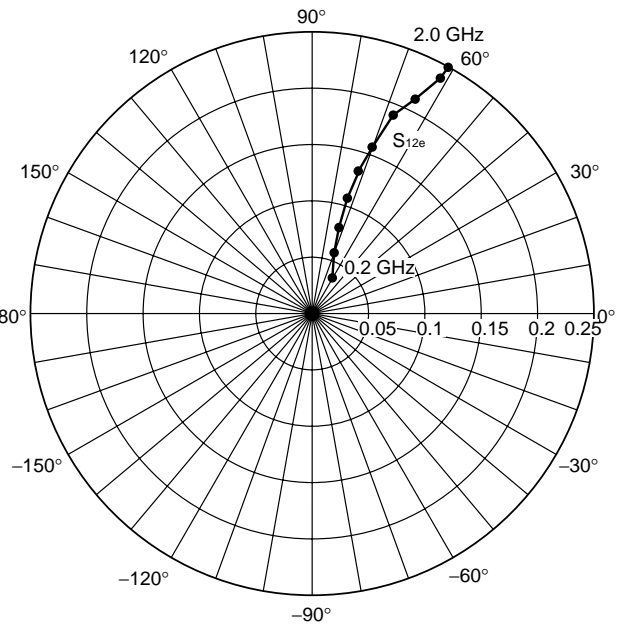
S_{21e}-FREQUENCY

CONDITION V_{CE} = 10 V
I_c = 20 mA



S_{12e}-FREQUENCY

CONDITION V_{CE} = 10 V
I_c = 20 mA



[MEMO]

[MEMO]

[MEMO]

No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.

www.s-manuals.com